Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z4d
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	147
Program Memory Size	1.5MB (1.5M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 27x10b, 5x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc564b64l7b8ecx

List of figures

Table 2. SPC564Bxx and SPC56ECxx family comparison[1] (continued)

Feature	SPC564B64		SPC56EC64			SPC564B70		SPC56EC70			SPC564B74		SPC56EC74		
Package	LQFP 176	LQFP 208	LQFP 176	LQFP 208	LBGA 256	LQFP 176	LQFP 208	LQFP 176	LQFP 208	LBGA 256	LQFP 176	LQFP 208	LQFP 176	LQFP 208	LBGA 256
FlexRay	Yes														
STCU[11]	Yes														
Ethernet	No		Yes			No		Yes			No		Yes		
I^2C	1														
32 kHz oscillator (SXOSC)	Yes														
GPIO[12]	147	177	147	177	199	147	177	147	177	199	147	177	147	177	199
Debug	JTAG				Nexus 3+	JTAG				Nexus 3+	JTAG				Nexus 3+
Cryptographic Services Engine (CSE)	Optional														

1. Feature set dependent on selected peripheral multiplexing; table shows example.
2. Based on 125 °C ambient operating temperature and subject to full device characterization.
3. The e200z0h can run at speeds up to 80 MHz. However, if system frequency is >80 MHz (e.g., e200z4d running at 120 MHz) the e200z0h needs to run at 1/2 system frequency. There is a configurable e200z0 system clock divider for this purpose.
4. DMAMUX also included that allows for software selection of 32 out of a possible 57 sources.
5. Not shared with 12-bit ADC, but possibly shared with other alternate functions.
6. There are 23 dedicated ANS plus 4 dedicated ANX channels on LQPF176. For higher pin count packages, there are 29 dedicated ANS plus 4 dedicated ANX channels.
7. 16x precision channels (ANP) and 3x standard (ANS).
8. Not shared with 10-bit ADC, but possibly shared with other alternate functions.
9. As a minimum, all timer channels can function as PWM or Input Capture and Output Control. Refer to the eMIOS section of the device reference manual for information on the channel configuration and functions.
10. CAN Sampler also included that allows ID of CAN message to be captured when in low power mode.
11. STCU controls MBIST activation and reporting.
12. Estimated I/O count for proposed packages based on multiplexing with peripherals.

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PA[10]	PCR[10]	AF0 AF1 AF2 AF3 — — —	GPIO[10] E0UC[10] SDA LIN2TX COL ADC1_S[2] SIN_1	SIUL eMIOS_0 I^2C LINFlexD_2 FEC ADC_1 DSPI_1	I/O I/O I/O O I I I	M/S	Tristate	131	155	A15
PA[11]	PCR[11]	AF0 AF1 AF2 AF3 — — — —	GPIO[11] E0UC[11] SCL — RX_ER EIRQ[16] LIN2RX ADC1_S[3]	SIUL eMIOS_0 I^2C — FEC SIUL LINFlexD_2 ADC_1	I/O I/O I/O — I I I I	M/S	Tristate	132	156	B14
PA[12]	PCR[12]	AF0 AF1 AF2 AF3 — —	GPIO[12] — E0UC[28] CS3_1 EIRQ[17] SIN_0	SIUL — eMIOS_0 DSPI1 SIUL DSPI_0	I/O — I/O O I I	S	Tristate	53	69	P6
PA[13]	PCR[13]	AF0 AF1 AF2 AF3	GPIO[13] SOUT_0 E0UC[29] —	SIUL DSPI_0 eMIOS_0 —	I/O O I/O —	M/S	Tristate	52	66	R5
PA[14]	PCR[14]	AF0 AF1 AF2 AF3 —	GPIO[14] SCK_0 CS0_0 E0UC[0] EIRQ[4]	SIUL DSPI_0 DSPI_0 eMIOS_0 SIUL	I/O I/O I/O I/O I	M/S	Tristate	50	58	P4
PA[15]	PCR[15]	AF0 AF1 AF2 AF3 —	GPIO[15] CS0_0 SCK_0 E0UC[1] WKPU[10]	SIUL DSPI_0 DSPI_0 eMIOS_0 WKPU	I/O I/O I/O I/O I	M/S	Tristate	48	56	R2

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PD[15]	PCR[63]	AF0 AF1 AF2 AF3 ALT4 —	GPIO[63] CS2_1 E0UC[27] — FR_DBG[1] ADC0_S[7]	SIUL DSPI_1 eMIOS_0 — Flexray ADC_0	I/O O I/O — O I	S	Tristate	106	128	J13
PE[0]	PCR[64]	AF0 AF1 AF2 AF3 — —	GPIO[64] E0UC[16] — — CAN5RX WKPU[6]	SIUL eMIOS_0 — — FlexCAN_5 WKPU	I/O I/O — — I I	S	Tristate	18	18	G2
PE[1]	PCR[65]	AF0 AF1 AF2 AF3	GPIO[65] E0UC[17] CAN5TX —	SIUL eMIOS_0 FlexCAN_5 —	I/O I/O O —	M/S	Tristate	20	20	F4
PE[2]	PCR[66]	AF0 AF1 AF2 AF3 ALT4 — —	GPIO[66] E0UC[18] — — FR_A_TX_EN SIN_1 EIRQ[21]	SIUL eMIOS_0 — — Flexray DSPI_1 SIUL	I/O I/O — — O I I	M/S	Tristate	156	180	A7
PE[3]	PCR[67]	AF0 AF1 AF2 AF3 — —	GPIO[67] E0UC[19] SOUT_1 — FR_A_RX WKPU[29]	SIUL eMIOS_0 DSPI_1 — Flexray WKPU	I/O I/O O — I I	M/S	Tristate	157	181	A10
PE[4]	PCR[68]	AF0 AF1 AF2 AF3 ALT4 —	GPIO[68] E0UC[20] SCK_1 — FR_B_TX EIRQ[9]	SIUL eMIOS_0 DSPI_1 — Flexray SIUL	I/O I/O I/O — O I	M/S	Tristate	160	184	A8

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PF[8]	PCR[88]	AF0 AF1 AF2 AF3	GPIO[88] CAN3TX CS4_0 CAN2TX	SIUL FlexCAN_3 DSPI_0 FlexCAN_2	I/O O O O	M/S	Tristate	42	50	N2
PF[9]	PCR[89]	AF0 AF1 AF2 AF3 — — —	GPIO[89] E1UC[1] CS5_0 — CAN2RX CAN3RX WKPU[22]	SIUL eMIOS_1 DSPI_0 — FlexCAN_2 FlexCAN_3 WKPU	I/O I/O O — I I I	S	Tristate	41	49	M4
PF[10]	PCR[90]	AF0 AF1 AF2 AF3	GPIO[90] CS1_0 LIN4TX E1UC[2]	SIUL DSPI_0 LINFlexD_4 eMIOS_1	I/O O O I/O	M/S	Tristate	46	54	P2
PF[11]	PCR[91]	AF0 AF1 AF2 AF3 — —	GPIO[91] CS2_0 E1UC[3] — LIN4RX WKPU[15]	SIUL DSPI_0 eMIOS_1 — LINFlexD_4 WKPU	I/O O I/O — I I	S	Tristate	47	55	R1
PF[12]	PCR[92]	AF0 AF1 AF2 AF3	GPIO[92] E1UC[25] LIN5TX —	SIUL eMIOS_1 LINFlexD_5 —	I/O I/O O —	M/S	Tristate	43	51	P1
PF[13]	PCR[93]	AF0 AF1 AF2 AF3 — —	GPIO[93] E1UC[26] — — LIN5RX WKPU[16]	SIUL eMIOS_1 — — LINFlexD_5 WKPU	I/O I/O — — I I	S	Tristate	49	57	P3

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PH[8]	PCR[120]	AF0 AF1 AF2 AF3	GPIO[120] E1UC[10] CS2_2 MA[0]	SIUL eMIOS_1 DSPI_2 ADC_0	I/O I/O O O	M/S	Tristate	166	190	A6
PH[9][6]	PCR[121]	AF0 AF1 AF2 AF3 —	GPIO[121] — — — TCK	SIUL — — — JTAGC	I/O — — — I	S	Input, weak pull-up	155	179	A11
PH[10][6]	PCR[122]	AF0 AF1 AF2 AF3 —	GPIO[122] — — — TMS	SIUL — — — JTAGC	I/O — — — I	M/S	Input, weak pull-up	148	172	D10
PH[11]	PCR[123]	AF0 AF1 AF2 AF3	GPIO[123] SOUT_3 CS0_4 E1UC[5]	SIUL DSPI_3 DSPI_4 eMIOS_1	I/O O I/O I/O	M/S	Tristate	140	164	A13
PH[12]	PCR[124]	AF0 AF1 AF2 AF3	GPIO[124] SCK_3 CS1_4 E1UC[25]	SIUL DSPI_3 DSPI_4 eMIOS_1	I/O I/O O I/O	M/S	Tristate	141	165	B12
PH[13]	PCR[125]	AF0 AF1 AF2 AF3	GPIO[125] SOUT_4 CS0_3 E1UC[26]	SIUL DSPI_4 DSPI_3 eMIOS_1	I/O O I/O I/O	M/S	Tristate	9	9	B1
PH[14]	PCR[126]	AF0 AF1 AF2 AF3	GPIO[126] SCK_4 CS1_3 E1UC[27]	SIUL DSPI_4 DSPI_3 eMIOS_1	I/O I/O O I/O	M/S	Tristate	10	10	C1
PH[15]	PCR[127]	AF0 AF1 AF2 AF3	GPIO[127] SOUT_5 — E1UC[17]	SIUL DSPI_5 — eMIOS_1	I/O O — I/O	M/S	Tristate	8	8	E3

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PI[7]	PCR[135]	AF0 AF1 AF2 AF3 ALT4	GPIO[135] E1UC[31] CS1_4 CS1_5 CS1_6	SIUL eMIOS_1 DSPI_4 DSPI_5 DSPI_6	I/O I/O O O O	S	Tristate	12	12	E2
PI[8]	PCR[136]	AF0 AF1 AF2 AF3 —	GPIO[136] — — — ADC0_S[16]	SIUL — — — ADC_0	I/O — — — I	S	Tristate	108	130	J14
PI[9]	PCR[137]	AF0 AF1 AF2 AF3 —	GPIO[137] — — — ADC0_S[17]	SIUL — — — ADC_0	I/O — — — I	S	Tristate	—	131	J15
PI[10]	PCR[138]	AF0 AF1 AF2 AF3 —	GPIO[138] — — — ADC0_S[18]	SIUL — — — ADC_0	I/O — — — I	S	Tristate	—	134	J16
PI[11]	PCR[139]	AF0 AF1 AF2 AF3 — —	GPIO[139] — — — ADC0_S[19] SIN_3	SIUL — — — ADC_0 DSPI_3	I/O — — — I I	S	Tristate	111	135	H16
PI[12]	PCR[140]	AF0 AF1 AF2 AF3 —	GPIO[140] CS0_3 CS0_2 — ADC0_S[20]	SIUL DSPI_3 DSPI_2 — ADC_0	I/O I/O I/O — I	S	Tristate	112	136	G15

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PJ[10]	PCR[154]	AF0 AF1 AF2 AF3 —	GPIO[154] — — — ADC1_S[9]	SIUL — — — ADC_1	I/O — — — I	S	Tristate	—	67	T5
PJ[11]	PCR[155]	AF0 AF1 AF2 AF3 —	GPIO[155] — — — ADC1_S[10]	SIUL — — — ADC_1	I/O — — — I	S	Tristate	—	60	R3
PJ[12]	PCR[156]	AF0 AF1 AF2 AF3 —	GPIO[156] — — — ADC1_S[11]	SIUL — — — ADC_1	I/O — — — I	S	Tristate	—	59	T1
PJ[13]	PCR[157]	AF0 AF1 AF2 AF3 — — — —	GPIO[157] — CS1_7 — CAN4RX ADC1_S[12] CAN1RX WKPU[31]	SIUL — DSPI_7 — FlexCAN_4 ADC_1 FlexCAN_1 WKPU	I/O — O — I I I I	S	Tristate	—	65	N5
PJ[14]	PCR[158]	AF0 AF1 AF2 AF3	GPIO[158] CAN1TX CAN4TX CS2_7	SIUL FlexCAN_1 FlexCAN_4 DSPI_7	I/O O O O	M/S	Tristate	—	64	T4
PJ[15]	PCR[159]	AF0 AF1 AF2 AF3 —	GPIO[159] — CS1_6 — CAN1RX	SIUL — DSPI_6 — FlexCAN_1	I/O — O — I	M/S	Tristate	—	63	R4

8. Guaranteed by device validation.

Note: SRAM retention guaranteed to LVD levels.

3.5 Thermal characteristics

3.5.1 Package thermal characteristics

Table 12. LQFP thermal characteristics(1)

Symbol		C	Parameter	Conditions(2)	Pin count	Value(3)			Unit
						Min	Typ	Max	
$R_{\theta JA}$	CC	D	Thermal resistance, junction-to-ambient natural convection	Single-layer board—1s	176	—	—	44.4(4)	°C/W
					208	—	—	43	°C/W
$R_{\theta JA}$	CC	D	Thermal resistance, junction-to-ambient natural convection	Four-layer board—2s2p(5)	176	—	—	36.1	°C/W
					208	—	—	33.9	°C/W

1. Thermal characteristics are targets based on simulation that are subject to change per device characterization.
2. V_{DD} = 3.3 V ± 10 % / 5.0 V ± 10 %, T_A = –40 to 125 °C.
3. All values need to be confirmed during device validation.
4. 1s board as per standard JEDEC (JESD51-7) in natural convection.
5. 2s2p board as per standard JEDEC (JESD51-7) in natural convection.

Table 13. LBGA256 thermal characteristics(1)

Symbol		C	Parameter	Conditions	Value	Unit
$R_{\theta JA}$	CC	—	Thermal resistance, junction-to-ambient natural convection	Single-layer board—1s	44.3	°C/W
				Four-layer board—2s2p	31	

1. Thermal characteristics are targets based on simulation that are subject to change per device characterization.

3.5.2 Power considerations

The average chip-junction temperature, T_J, in degrees Celsius, may be calculated using *Equation 1*:

Equation 1 $T_J = T_A + (P_D \times R_{\theta JA})$

Where:

T_A is the ambient temperature in °C.

$R_{\theta JA}$ is the package junction-to-ambient thermal resistance, in °C/W.

P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$).

P_{INT} is the product of I_{DD} and V_{DD}, expressed in watts. This is the chip internal power.

$P_{I/O}$ represents the power dissipation on input and output pins; user determined.

Most of the time for the applications, $P_{I/O} < P_{INT}$ and may be neglected. On the other hand, $P_{I/O}$ may be significant, if the device is configured to continuously drive external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

Equation 2 $P_D = K / (T_J + 273\ °C)$

Therefore, solving equations *Equation 1* and *Equation 2*:

Equation 3 $K = P_D \times (T_A + 273\ °C) + R_{\theta JA} \times P_D^2$

Where:

K is a constant for the particular part, which may be determined from *Equation 3* by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J may be obtained by solving equations *Equation 1* and *Equation 2* iteratively for any value of T_A.

3.6 I/O pad electrical characteristics

3.6.1 I/O pad types

The device provides four main I/O pad types depending on the associated alternate functions:

- Slow pads—These pads are the most common pads, providing a good compromise between transition time and low electromagnetic emission.
- Medium pads—These pads provide transition fast enough for the serial communication channels with controlled current to reduce electromagnetic emission.
- Fast pads—These pads provide maximum speed. These are used for improved Nexus debugging capability.
- Input only pads—These pads are associated to ADC channels and 32 kHz low power external crystal oscillator providing low input leakage.
- Low power pads—These pads are active in standby mode for wakeup source.

Also, medium/slow and fast/medium pads are available in design which can be configured to behave like a slow/medium and medium/fast pads depending upon the slew-rate control.

Figure 11. Fast external crystal oscillator (4 to 40 MHz) electrical characteristics

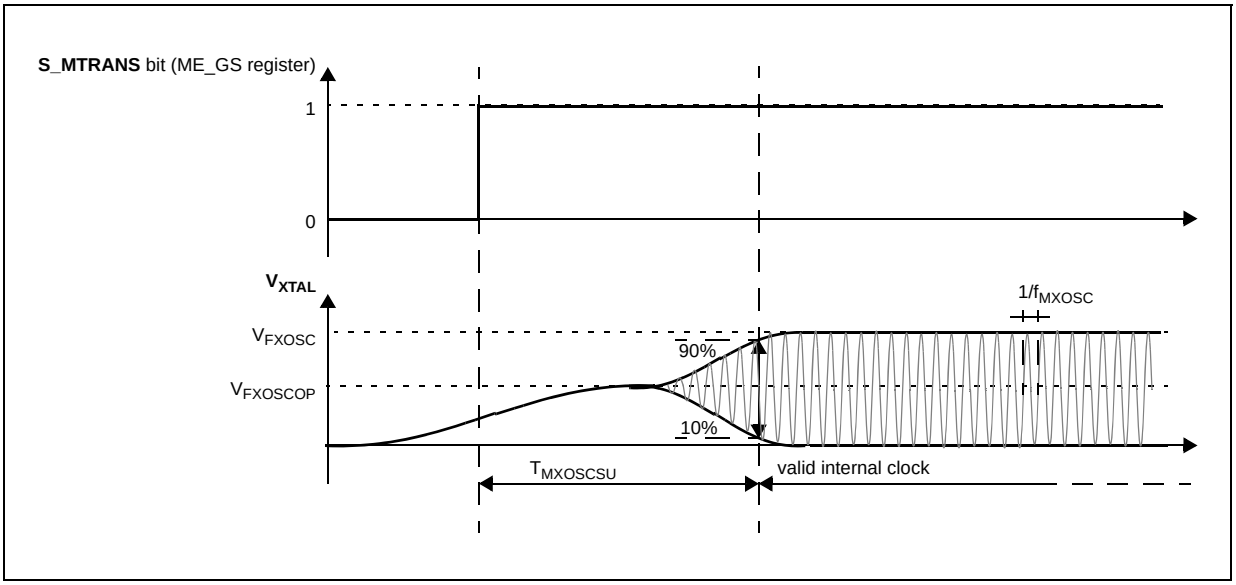


Table 36. Fast external crystal oscillator (4 to 40 MHz) electrical characteristics

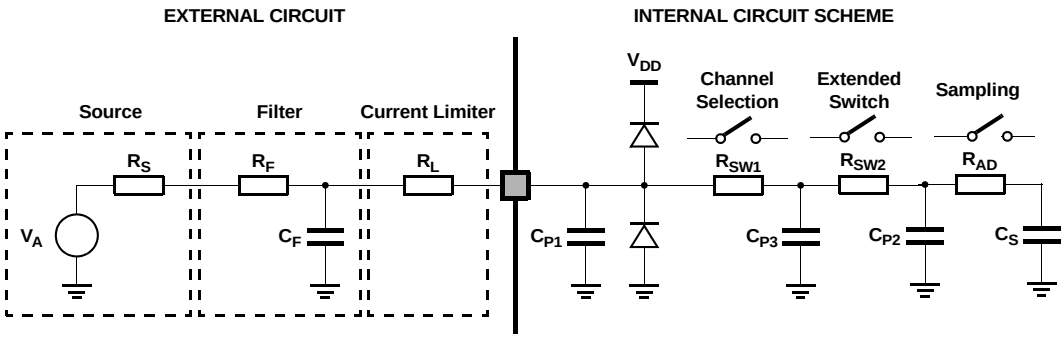
Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
f_{FXOSC}	SR	—	Fast external crystal oscillator frequency	—	4.0	—	40.0	MHz
g_{mFXOSC}	CC	C	Fast external crystal oscillator transconductance	V_{DD} = 3.3 V ± 10%	4[3]	—	20[3]	mA/V
				V_{DD} = 5.0 V ± 10%	6.5[3]	—	25[3]	
V_{FXOSC}	CC	T	Oscillation amplitude at EXTAL	f_{OSC} = 40 MHz For both V_{DD} = 3.3 V ± 10%, V_{DD} = 5.0 V ± 10%	—	0.95	—	V
$V_{FXOSCOP}$	CC	P	Oscillation operating point	—	—	1.8		V
I_{FXOSC}[4]	CC	T	Fast external crystal oscillator consumption	V_{DD} = 3.3 V ± 10%, f_{OSC} = 40 MHz	—	2	2.2	mA
				V_{DD} = 5.0 V ± 10%, f_{OSC} = 40 MHz	—	2.3	2.5	
				V_{DD} = 3.3 V ± 10%, f_{OSC} = 16 MHz	—	1.3	1.5	
				V_{DD} = 5.0 V ± 10%, f_{OSC} = 16 MHz	—	1.6	1.8	
$T_{FXOSCSU}$	CC	T	Fast external crystal oscillator start-up time	f_{OSC} = 40 MHz For both V_{DD} = 3.3 V ± 10%, V_{DD} = 5.0 V ± 10%	—	—	5	ms

Table 40. Fast internal RC oscillator (16 MHz) electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1]		Value[2]			Unit
						Min	Typ	Max	
$I_{FIRCRUN}$[3]	CC	T	Fast internal RC oscillator high frequency current in running mode	T_A = 25 °C, trimmed		—	—	200	µA
$I_{FIRCPWD}$	CC	D	Fast internal RC oscillator high frequency current in power down mode	T_A = 25 °C		—	—	100	nA
		D		T_A = 55 °C		—	—	200	nA
		D		T_A = 125 °C		—	—	1	µA
$I_{FIRCSTOP}$	CC	T	Fast internal RC oscillator high frequency and system clock current in stop mode	T_A = 25 °C	sysclk = off	—	500	—	µA
					sysclk = 2 MHz	—	600	—	
					sysclk = 4 MHz	—	700	—	
					sysclk = 8 MHz	—	900	—	
					sysclk = 16 MHz	—	1250	—	
T_{FIRCSU}	CC	C	Fast internal RC oscillator start-up time	T_A = 55 °C	V_{DD} = 5.0 V ± 10%	—	—	2.0	µs
		—			V_{DD} = 3.3 V ± 10%	—	—	5	
		—		T_A = 125 °C	V_{DD} = 5.0 V ± 10%	—	—	2.0	
		—			V_{DD} = 3.3 V ± 10%	—	—	5	
$\Delta_{FIRCPRE}$	CC	C	Fast internal RC oscillator precision after software trimming of f_{FIRC}	T_A = 25 °C		–1	—	+1	%
$\Delta_{FIRCTRIM}$	CC	C	Fast internal RC oscillator trimming step	T_A = 25 °C		—	1.6		%
$\Delta_{FIRCVAR}$	CC	C	Fast internal RC oscillator variation over temperature and supply with respect to f_{FIRC} at T_A = 25 °C in high-frequency configuration	—		–5	—	+5	%

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. All values need to be confirmed during device validation.
3. This does not include consumption linked to clock tree toggling and peripherals consumption when RC oscillator is ON.

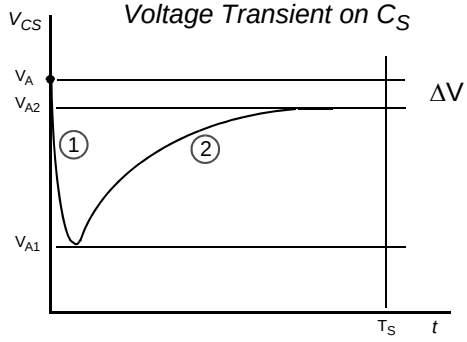
Figure 17. Input equivalent circuit (extended channels)



R_S Source Impedance
R_F Filter Resistance
C_F Filter Capacitance
R_L Current Limiter Resistance
R_{SW} Channel Selection Switch Impedance (two contributions R_{SW1} and R_{SW2})
R_{AD}Sampling Switch Impedance
C_P Pin Capacitance (three contributions, C_{P1}, C_{P2} and C_{P3})
C_S Sampling Capacitance

A second aspect involving the capacitance network shall be considered. Assuming the three capacitances C_F, C_{P1} and C_{P2} initially charged at the source voltage V_A (refer to the equivalent circuit reported in *Figure 16*): when the sampling phase is started (A/D switch close), a charge sharing phenomena is installed.

Figure 18. Transient behavior during sampling phase



$\Delta V < 0.5$ LSB

$\tau_1 < (R_{SW} + R_{AD})\, C_S << T_S$

$\tau_2 = R_L\,(C_S + C_{P1} + C_{P2})$

In particular two different transient periods can be distinguished:

- A first and quick charge transfer from the internal capacitance C_{P1} and C_{P2} to the sampling capacitance C_S occurs (C_S is supposed initially completely discharged): considering a worst case (since the time constant in reality would be faster) in which C_{P2} is reported in parallel to C_{P1} (call $C_P = C_{P1} + C_{P2}$), the two capacitances C_P and C_S are in series, and the time constant is

Equation 5

$$\tau_1 = (R_{SW} + R_{AD}) \bullet \frac{C_P \bullet C_S}{C_P + C_S}$$

This relation can again be simplified considering C_S as an additional worst condition. In reality, transient is faster, but the A/D converter circuitry has been designed to be robust also in very worst case: the sampling time T_s is always much longer than the internal time constant.

Equation 6

$$\tau_1 < (R_{SW} + R_{AD}) \bullet C_S \ll T_S$$

The charge of C_{P1} and C_{P2} is redistributed on C_S,determining a new value of the voltage V_{A1} on the capacitance according to the following equation

Equation 7

$$V_{A1} \bullet (C_S + C_{P1} + C_{P2}) = V_A \bullet (C_{P1} + C_{P2})$$

A second charge transfer involves also C_F (that is typically bigger than the on-chip capacitance) through the resistance RL: again considering the worst case in which C_{P2} and C_S were in parallel to C_{P1} (since the time constant in reality would be faster), the time constant is:

Equation 8

$$\tau_2 < R_L \bullet (C_S + C_{P1} + C_{P2})$$

In this case, the time constant depends on the external circuit: in particular imposing that the transient is completed well before the end of sampling time T_S, a constraints on R_L sizing is obtained:

Equation 9

$$8.5 \bullet \tau_2 = 8.5 \bullet R_L \bullet (C_S + C_{P1} + C_{P2}) < T_S$$

Of course, R_L shall be sized also according to the current limitation constraints, in combination with R_S (source impedance) and R_F (filter resistance). Being C_F definitively bigger than C_{P1}, C_{P2} and C_S, then the final voltage V_{A2} (at the end of the charge transfer transient) will be much higher than V_{A1}. The following equation must be respected (charge balance assuming now C_S already charged at V_{A1}):

Equation 10

$$V_{A2} \bullet (C_S + C_{P1} + C_{P2} + C_F) = V_A \bullet C_F + V_{A1} \bullet (C_{P1} + C_{P2} + C_S)$$

The two transients above are not influenced by the voltage source that, due to the presence of the R_FC_F filter, is not able to provide the extra charge to compensate the voltage drop on C_S with respect to the ideal source V_A; the time constant R_FC_F of the filter is very high with respect to the sampling time (T_S). The filter is typically designed to act as anti-aliasing

3.18.2 MII Transmit Signal Timing (TXD[3:0], TX_EN, TX_ER, TX_CLK)

The transmitter functions correctly up to a TX_CLK maximum frequency of 25 MHz +1%. There is no minimum frequency requirement. In addition, the system clock frequency must exceed four times the TX_CLK frequency in 2:1 mode and two times the TX_CLK frequency in 1:1 mode.

The transmit outputs (TXD[3:0], TX_EN, TX_ER) can be programmed to transition from either the rising or falling edge of TX_CLK, and the timing is the same in either case. This options allows the use of non-compliant MII PHYs.

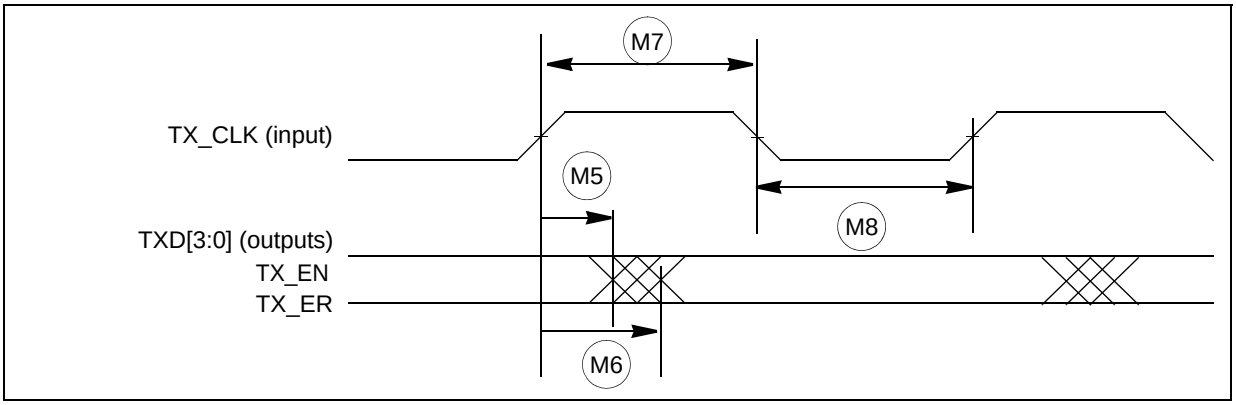
Refer to the Fast Ethernet Controller (FEC) chapter of the SPC564B74 and SPC56EC74 Reference Manual for details of this option and how to enable it.

Table 46. MII transmit signal timing(1)

Spec	Characteristic	Min	Max	Unit
M5	TX_CLK to TXD[3:0], TX_EN, TX_ER invalid	5	—	ns
M6	TX_CLK to TXD[3:0], TX_EN, TX_ER valid	—	25	ns
M7	TX_CLK pulse width high	35%	65%	TX_CLK period
M8	TX_CLK pulse width low	35%	65%	TX_CLK period

1. Output pads configured with SRE = 0b11.

Figure 22. MII transmit signal timing diagram



3.18.3 MII Async Inputs Signal Timing (CRS and COL)

Table 47. MII Async Inputs Signal Timing(1)

Spec	Characteristic	Min	Max	Unit
M9	CRS, COL minimum pulse width	1.5	—	TX_CLK period

1. Output pads configured with SRE = 0b11.

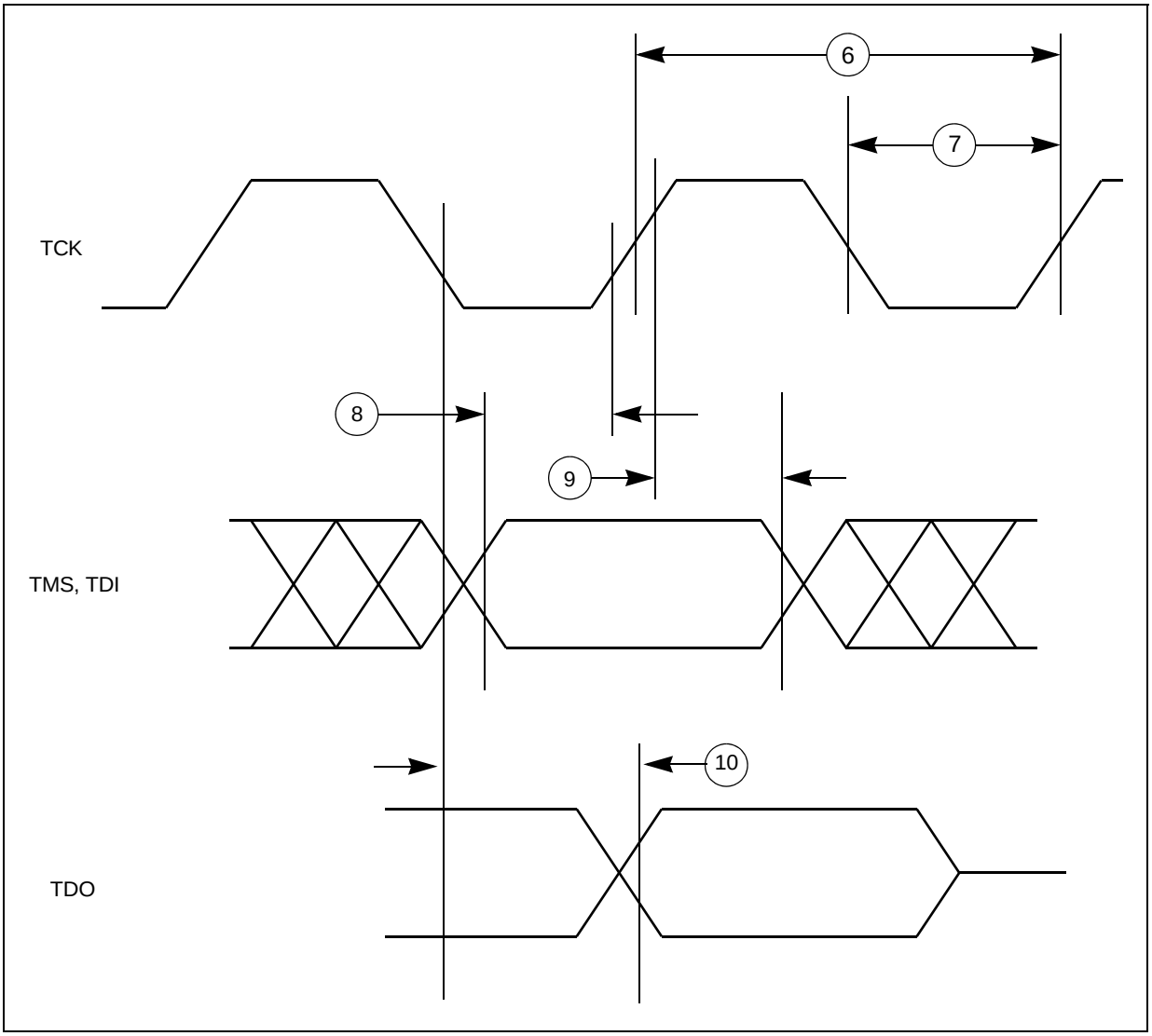
3.19 On-chip peripherals

3.19.1 Current consumption

Table 49. On-chip peripherals current consumption(1)

Symbol		C	Parameter	Conditions		Value(2) Typ	Unit
$I_{DD\_HV\_A(CAN)}$	CC	D	CAN (FlexCAN) supply current on $V_{DD\_HV\_A}$	500 Kbps	Total (static + dynamic) consumption: FlexCAN in loop-back mode XTAL@8 MHz used as CAN engine clock source Message sending period is 580 µs	$7.652 \times f_{periph} + 84.73$	µA
				125 Kbps		$8.0743 \times f_{periph} + 26.757$	
$I_{DD\_HV\_A(eMIOS)}$	CC	D	eMIOS supply current on $V_{DD\_HV\_A}$	Static consumption: eMIOS channel OFF Global prescaler enabled		$28.7 \times f_{periph}$	
				Dynamic consumption: It does not change varying the frequency (0.003 mA)		3	
$I_{DD\_HV\_A(SCI)}$	CC	D	SCI (LINFlex) supply current on $V_{DD\_HV\_A}$	Total (static + dynamic) consumption: LIN mode Baudrate: 20 Kbps		$4.7804 \times f_{periph} + 30.946$	
$I_{DD\_HV\_A(SPI)}$	CC	D	SPI (DSPI) supply current on $V_{DD\_HV\_A}$	Ballast static consumption (only clocked)		1	
				Ballast dynamic consumption (continuous communication): Baudrate: 2 Mbit Transmission every 8 µs Frame: 16 bits		$16.3 \times f_{periph}$	
$I_{DD\_HV\_A(ADC)}$	CC	D	ADC supply current on $V_{DD\_HV\_A}$	V_{DD} = 5.5 V	Ballast static consumption (no conversion)	$0.0409 \times f_{periph}$	mA
				V_{DD} = 5.5 V	Ballast dynamic consumption (continuous conversion)	$0.0049 \times f_{periph}$	

Figure 35. Nexus TDI, TMS, TDO timing



3.19.4 JTAG characteristics

Table 52. JTAG characteristics

No.	Symbol		C	Parameter	Value			Unit
					Min	Typ	Max	
1	t_{JCYC}	CC	D	TCK cycle time	64	—	—	ns
2	t_{TDIS}	CC	D	TDI setup time	10	—	—	ns
3	t_{TDIH}	CC	D	TDI hold time	5	—	—	ns
4	t_{TMSS}	CC	D	TMS setup time	10	—	—	ns
5	t_{TMSH}	CC	D	TMS hold time	5	—	—	ns
6	t_{TDOV}	CC	D	TCK low to TDO valid	—	—	33	ns

Table 53. LQFP176 mechanical data[1]

Symbol	mm			inches[2]		
	Min	Typ	Max	Min	Typ	Max
A	1.400		1.600			0.063
A1	0.050		0.150	0.002		
A2	1.350		1.450	0.053		0.057
b	0.170		0.270	0.007		0.011
C	0.090		0.200	0.004		0.008
D	23.900		24.100	0.941		0.949
E	23.900		24.100	0.941		0.949
e		0.500			0.020	
HD	25.900		26.100	1.020		1.028
HE	25.900		26.100	1.020		1.028
L[3]	0.450		0.750	0.018		0.030
L1		1.000			0.039	
ZD		1.250			0.049	
ZE		1.250			0.049	
q	0 °		7 °	0 °		7 °
Tolerance	mm			inches		
ccc	0.080			0.0031		

1. Controlling dimension: millimeter.
2. Values in inches are converted from mm and rounded to 4 decimal digits.
3. L dimension is measured at gauge plane at 0.25 mm above the seating plane.

Appendix A Abbreviations

Table 56 lists abbreviations used but not defined elsewhere in this document.

Table 56. Abbreviations

Abbreviation	Meaning
CS	Chip select
EVTO	Event out
MCKO	Message clock out
MDO	Message data out
MSEO	Message start/end out
MTFE	Modified timing format enable
SCK	Serial communications clock
SOUT	Serial data out
TBD	To be defined
TCK	Test clock input
TDI	Test data input
TDO	Test data output
TMS	Test mode select